

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Battery protection

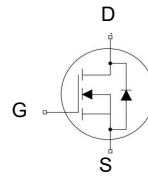
Ordering Information:

Part NO.	ZMSA015N08HR
Marking	ZMS015N08H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2000

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V _{DS}		80	V
Gate-Source Voltage ^①	V _{GS}		±20	V
Continuous Drain Current	I _D	T _C =25°C	240	A
	I _D	T _C =75°C	194	A
	I _D	T _C =100°C	168	A
Pulsed Drain Current	I _{DM}	Pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C;	720	A
Total Power Dissipation	P _D	T _C =25°C	250	W
Total Power Dissipation	P _D	T _A =25°C	5.0	W
Operating Junction Temperature	T _J		-55 to +175	°C
Storage Temperature	T _{STG}		-55 to +175	°C
Single Pulse Avalanche Energy	E _{AS}	L=0.1mH, V _{GS} =10V, R _g =25Ω,	310	mJ
		L=0.5mH, V _{GS} =10V, R _g =25Ω,	713	mJ
ESD Level (HBM)	CLASS 2			

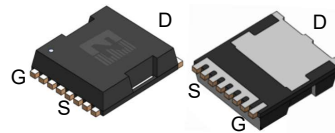
Product Summary



$$V_{DS} = 80V$$

$$R_{DS(ON)} = 1.6m\Omega$$

$$I_D = 240A$$



TOLL



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.6	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{②}$		-	30	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	3.3	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=80V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$		1.6	2.1	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=20A$		28		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=30A$		0.81	1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=40V$	-	7547	-	pF
Output capacitance	C_{oss}		-	1671	-	
Reverse transfer capacitance	C_{rss}		-	46	-	
Gate Resistance	R_g	$f=1MHz$	-	2.5		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	121	-	nC
Gate - Source charge	Q_{gs}		-	24	-	
Gate - Drain charge	Q_{gd}		-	23	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	19	-	ns
Turn-ON Rise time	t_r		-	14	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	31	-	ns
Turn-Off Fall time	t_f		-	37	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, di_S/dt=100A/\mu s, I_S=50A$	-	76	-	ns
Reverse Recovery Charge	Q_{RR}		-	120	-	nC

Fig.1 Gate-Charge Characteristics

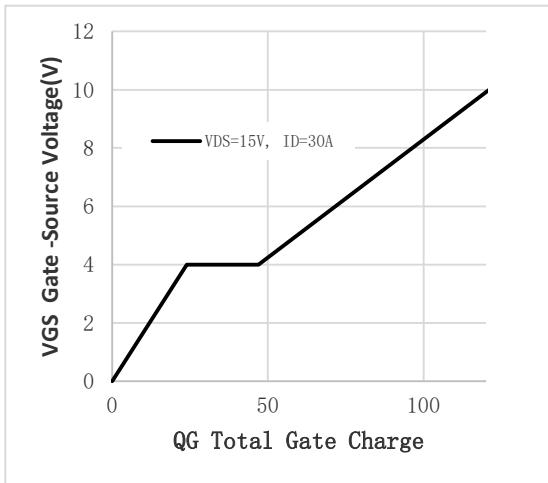


Fig.2 Capacitance Characteristics

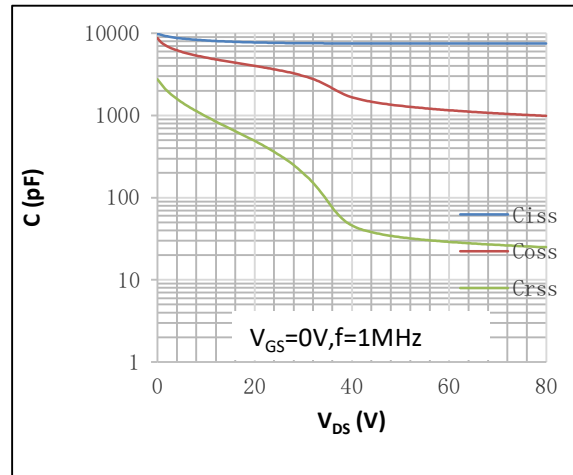


Fig.3 Power Dissipation

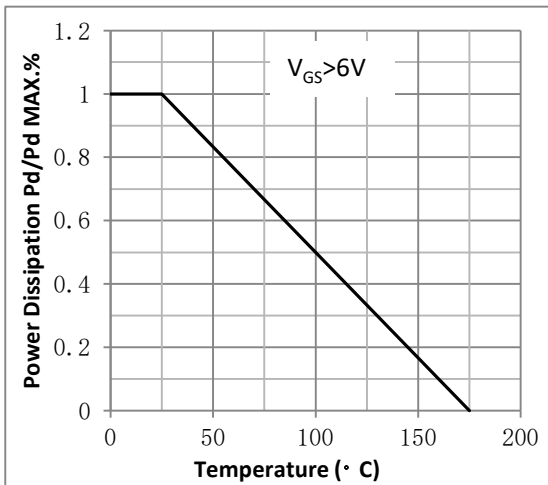


Fig.4 Typical output Characteristics

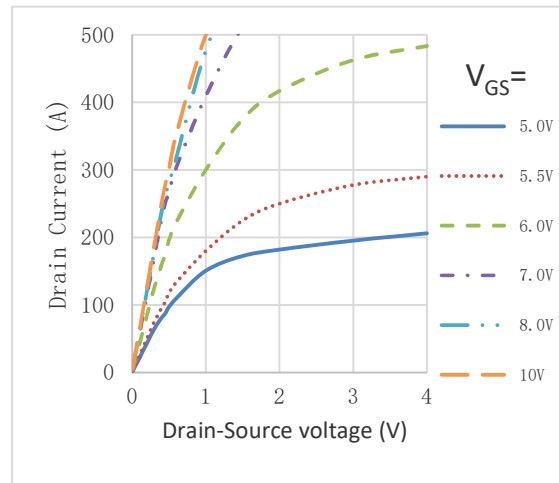


Fig.5 Threshold Voltage V.S Junction Temperature

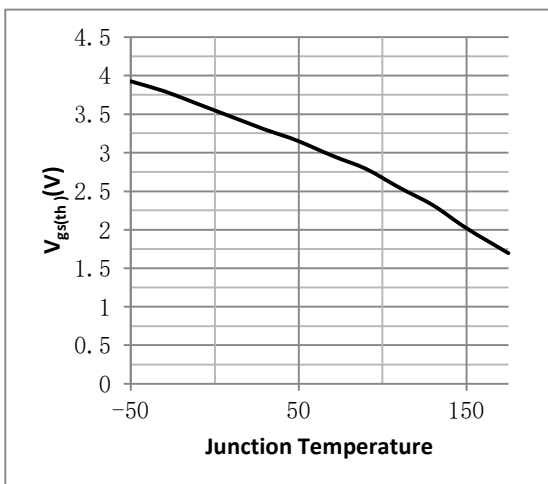


Fig.6 Resistance V.S Drain Current

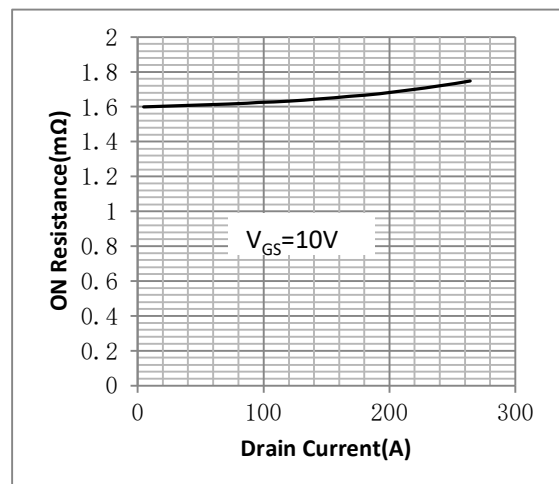


Fig.7 On-Resistance VS Gate Source Voltage

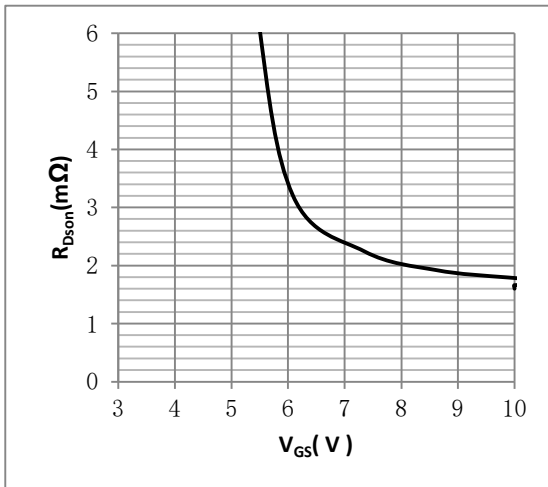


Fig.8 On-Resistance V.S Junction Temperature

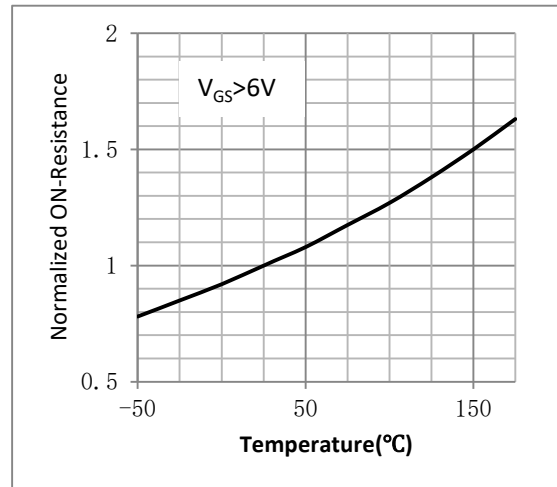


Figure 9. Diode Forward Voltage vs. Current

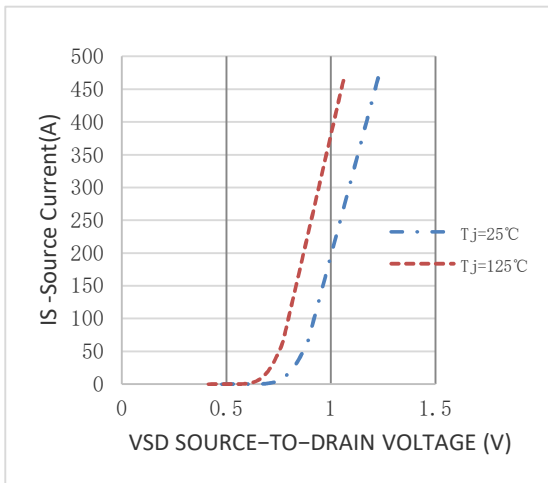


Figure 10. Transfer Characteristics

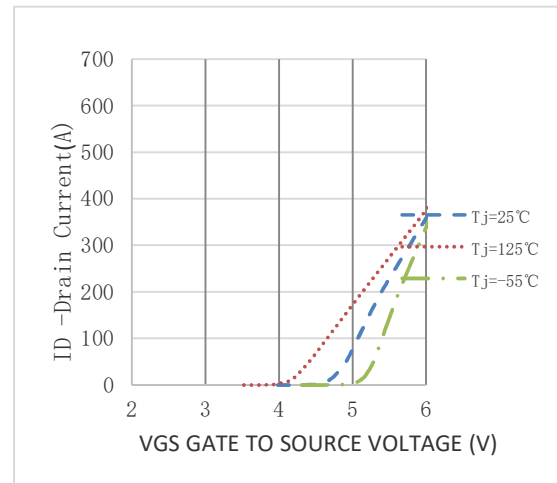


Fig.11 Safe Operating Area

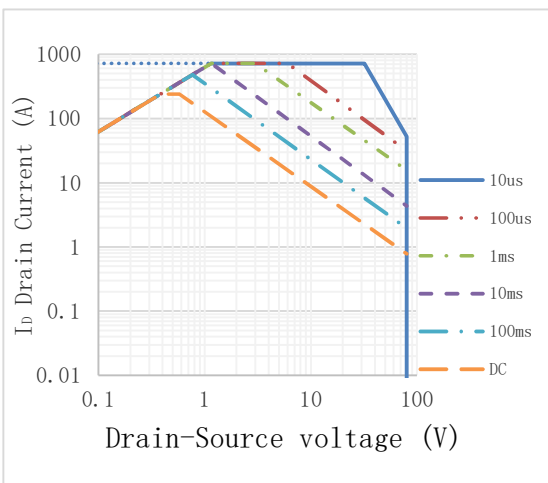
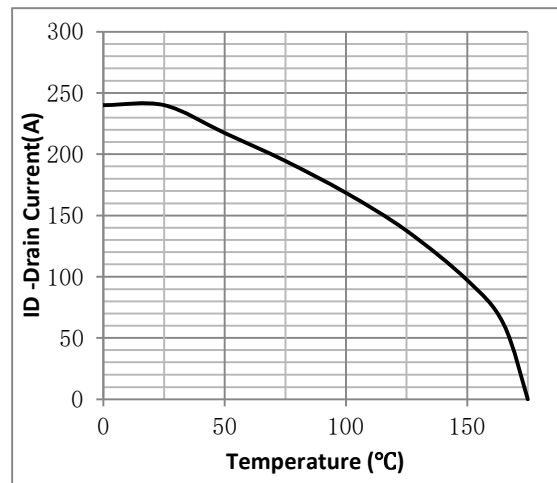
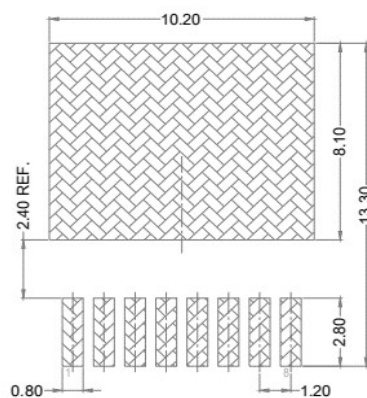
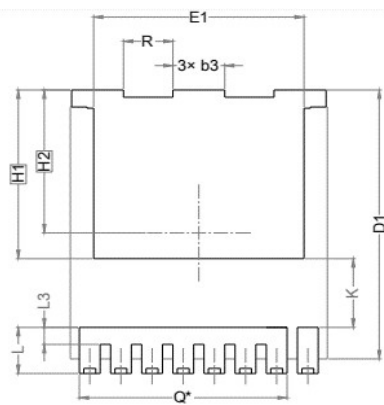
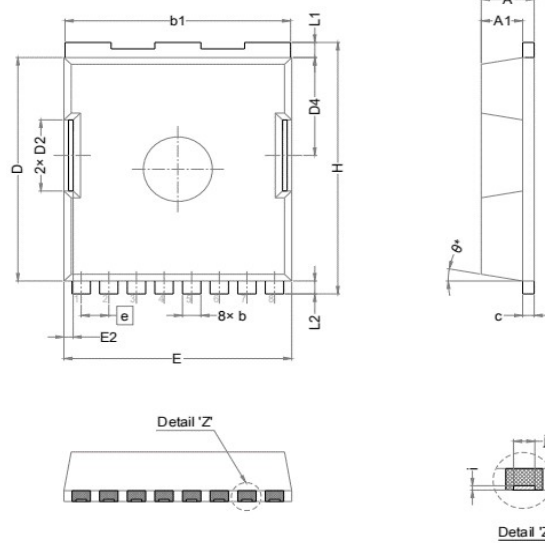


Fig.12 ID vs. Case Temperature^③



•TOLL Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b3	1.90	2.00	2.10
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D4	4.45	4.55	4.65
E	9.80	9.90	10.00
E1	8.00	8.10	8.20
E2	0.30	0.40	0.50
e	1.20 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
H2	5.89 BSC		
i	0.10 REF.		
j	0.46 REF.		
K	2.80 REF.		
L	1.60	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.60	0.70	0.80
N	8		
Q	6.80 REF.		
R	1.80	1.90	2.00
θ	10° REF.		



Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2021.9.6	
B	2022.9.5	1.Add Reach,HF figure,2.ID modify
C	2025.7.4	1. Update Cg condition and curve. 2. Add VFSD typical value.